



# STGP19NC60H STGW19NC60H

19 A - 600 V - very fast IGBT

## Features

- Low on-voltage drop ( $V_{CE(sat)}$ )
- High input impedance (voltage driven)

## Applications

- High frequency motor controls
- SMPS and PFC in both hard switch and resonant topologies

## Description

This IGBT utilizes the advanced PowerMESH™ process resulting in an excellent trade-off between switching performance and low on-state behavior.

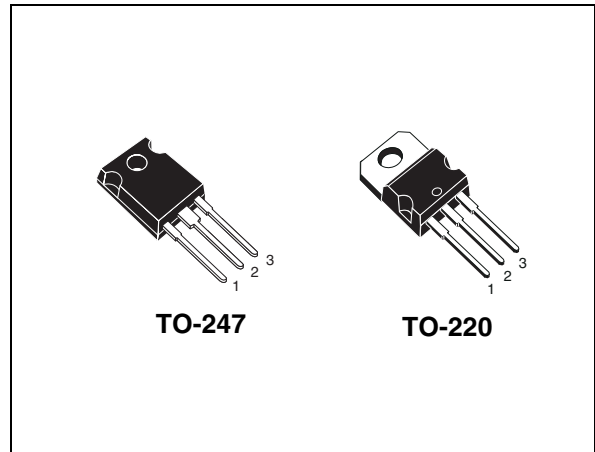


Figure 1. Internal schematic diagram

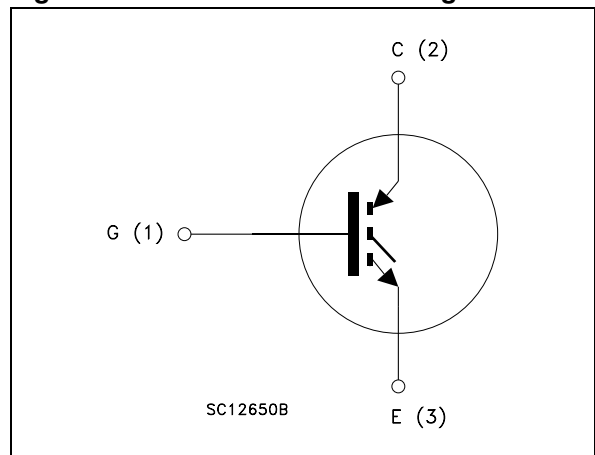


Table 1. Device summary

| Order codes | Marking   | Package | Packaging |
|-------------|-----------|---------|-----------|
| STGW19NC60H | GW19NC60H | TO-247  | Tube      |
| STGP19NC60H | GP19NC60H | TO-220  | Tube      |

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

| Symbol         | Parameter                                               | Value       |        | Unit |
|----------------|---------------------------------------------------------|-------------|--------|------|
|                |                                                         | TO-247      | TO-220 |      |
| $V_{CES}$      | Collector-emitter voltage ( $V_{GE}=0$ )                | 600         |        | V    |
| $I_C^{(1)}$    | Collector current (continuous) at $T_C = 25\text{ °C}$  | 42          | 40     | A    |
| $I_C^{(1)}$    | Collector current (continuous) at $T_C = 100\text{ °C}$ | 21          | 19     | A    |
| $I_{CL}^{(2)}$ | Turn-off latching current                               | 40          |        | A    |
| $I_{CP}^{(3)}$ | Pulsed collector current                                | 40          |        | A    |
| $V_{GE}$       | Gate-emitter voltage                                    | $\pm 20$    |        | V    |
| $P_{TOT}$      | Total dissipation at $T_C = 25\text{ °C}$               | 140         | 130    | W    |
| $T_j$          | Operating junction temperature                          | – 55 to 150 |        | °C   |

1. Calculated according to the iterative formula:

$$I_C(T_C) = \frac{T_{JMAX} - T_C}{R_{THJ-C} \times V_{CESAT(MAX)}(T_C, I_C)}$$

2.  $V_{clamp} = 80\%(V_{CES})$ ,  $T_j = 150\text{ °C}$ ,  $R_G = 10\text{ }\Omega$ ,  $V_{GE} = 15\text{ V}$

3. Pulse width limited by max. junction temperature allowed

**Table 3. Thermal resistance**

| Symbol         | Parameter                                | Value  |        | Unit |
|----------------|------------------------------------------|--------|--------|------|
|                |                                          | TO-247 | TO-220 |      |
| $R_{thj-case}$ | Thermal resistance junction-case max.    | 0.9    | 0.95   | °C/W |
| $R_{thj-amb}$  | Thermal resistance junction-ambient max. | 50     | 62.5   | °C/W |

## 2 Electrical characteristics

( $T_{CASE}=25^{\circ}\text{C}$  unless otherwise specified)

**Table 4. Static**

| Symbol         | Parameter                                          | Test conditions                                                                                                  | Min. | Typ.       | Max.      | Unit                |
|----------------|----------------------------------------------------|------------------------------------------------------------------------------------------------------------------|------|------------|-----------|---------------------|
| $V_{BR(CES)}$  | Collector-emitter breakdown voltage ( $V_{GE}=0$ ) | $I_C = 1\text{ mA}$                                                                                              | 600  |            |           | V                   |
| $V_{CE(sat)}$  | Collector-emitter saturation voltage               | $V_{GE}=15\text{ V}$ , $I_C=12\text{ A}$<br>$V_{GE}=15\text{ V}$ , $I_C=12\text{ A}$ , $T_C=125^{\circ}\text{C}$ |      | 1.8<br>1.6 | 2.5       | V<br>V              |
| $V_{GE(th)}$   | Gate threshold voltage                             | $V_{CE}=V_{GE}$ , $I_C=250\text{ }\mu\text{A}$                                                                   | 3.75 |            | 5.75      | V                   |
| $I_{CES}$      | Collector cut-off current ( $V_{GE}=0$ )           | $V_{CE}=600\text{ V}$<br>$V_{CE}=600\text{ V}$ , $T_C=125^{\circ}\text{C}$                                       |      |            | 150<br>1  | $\mu\text{A}$<br>mA |
| $I_{GES}$      | Gate-emitter leakage current ( $V_{CE}=0$ )        | $V_{GE}=\pm 20\text{ V}$                                                                                         |      |            | $\pm 100$ | nA                  |
| $g_{fs}^{(1)}$ | Forward transconductance                           | $V_{CE}=15\text{ V}$ , $I_C=12\text{ A}$                                                                         |      | 5          |           | S                   |

1. Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

**Table 5. Dynamic**

| Symbol    | Parameter                    | Test conditions                                         | Min. | Typ. | Max. | Unit |
|-----------|------------------------------|---------------------------------------------------------|------|------|------|------|
| $C_{ies}$ | Input capacitance            | $V_{CE}=25\text{ V}$ , $f=1\text{ MHz}$ ,<br>$V_{GE}=0$ |      | 1180 |      | pF   |
| $C_{oes}$ | Output capacitance           |                                                         |      | 130  |      | pF   |
| $C_{res}$ | Reverse transfer capacitance |                                                         |      | 36   |      | pF   |
| $Q_g$     | Total gate charge            | $V_{CE}=390\text{ V}$ , $I_C=5\text{ A}$ ,              |      | 53   |      | nC   |
| $Q_{ge}$  | Gate-emitter charge          | $V_{GE}=15\text{ V}$ ,                                  |      | 10   |      | nC   |
| $Q_{gc}$  | Gate-collector charge        | Figure 18                                               |      | 23   |      | nC   |

**Table 6. Switching on/off (inductive load)**

| Symbol                                  | Parameter                                                         | Test conditions                                                                                                                                                  | Min. | Typ.             | Max. | Unit                   |
|-----------------------------------------|-------------------------------------------------------------------|------------------------------------------------------------------------------------------------------------------------------------------------------------------|------|------------------|------|------------------------|
| $t_{d(on)}$<br>$t_r$<br>$(di/dt)_{on}$  | Turn-on delay time<br>Current rise time<br>Turn-on current slope  | $V_{CC} = 390\text{ V}$ , $I_C = 12\text{ A}$<br>$R_G = 10\ \Omega$ , $V_{GE} = 15\text{ V}$ ,<br><a href="#">Figure 17</a>                                      |      | 25<br>7<br>1600  |      | ns<br>ns<br>A/ $\mu$ s |
| $t_{d(on)}$<br>$t_r$<br>$(di/dt)_{on}$  | Turn-on delay time<br>Current rise time<br>Turn-on current slope  | $V_{CC} = 390\text{ V}$ , $I_C = 12\text{ A}$<br>$R_G = 10\ \Omega$ , $V_{GE} = 15\text{ V}$ ,<br>$T_c = 125\text{ }^\circ\text{C}$<br><a href="#">Figure 17</a> |      | 24<br>8<br>1400  |      | ns<br>ns<br>A/ $\mu$ s |
| $t_{r(Voff)}$<br>$t_{d(Voff)}$<br>$t_f$ | Off voltage rise time<br>Turn-off delay time<br>Current fall time | $V_{CC} = 390\text{ V}$ , $I_C = 12\text{ A}$<br>$R_G = 10\ \Omega$ , $V_{GE} = 15\text{ V}$ ,<br><a href="#">Figure 17</a>                                      |      | 27<br>97<br>73   |      | ns<br>ns<br>ns         |
| $t_{r(Voff)}$<br>$t_{d(Voff)}$<br>$t_f$ | Off voltage rise time<br>Turn-off delay time<br>Current fall time | $V_{CC} = 390\text{ V}$ , $I_C = 12\text{ A}$<br>$R_G = 10\ \Omega$ , $V_{GE} = 15\text{ V}$ ,<br>$T_c = 125\text{ }^\circ\text{C}$<br><a href="#">Figure 17</a> |      | 58<br>144<br>128 |      | ns<br>ns<br>ns         |

**Table 7. Switching energy (inductive load)**

| Symbol                                  | Parameter                                                                       | Test conditions                                                                                                                                                  | Min. | Typ.              | Max. | Unit                          |
|-----------------------------------------|---------------------------------------------------------------------------------|------------------------------------------------------------------------------------------------------------------------------------------------------------------|------|-------------------|------|-------------------------------|
| $E_{on}$<br>$E_{off}^{(1)}$<br>$E_{ts}$ | Turn-on switching losses<br>Turn-off switching losses<br>Total switching losses | $V_{CC} = 390\text{ V}$ , $I_C = 12\text{ A}$<br>$R_G = 10\ \Omega$ , $V_{GE} = 15\text{ V}$ ,<br><a href="#">Figure 17</a>                                      |      | 85<br>189<br>274  |      | $\mu$ J<br>$\mu$ J<br>$\mu$ J |
| $E_{on}$<br>$E_{off}^{(1)}$<br>$E_{ts}$ | Turn-on switching losses<br>Turn-off switching losses<br>Total switching losses | $V_{CC} = 390\text{ V}$ , $I_C = 12\text{ A}$<br>$R_G = 10\ \Omega$ , $V_{GE} = 15\text{ V}$ ,<br>$T_c = 125\text{ }^\circ\text{C}$<br><a href="#">Figure 17</a> |      | 187<br>407<br>594 |      | $\mu$ J<br>$\mu$ J<br>$\mu$ J |

1. Turn-off losses include also the tail of the collector current

2.1 Electrical characteristics (curves)

Figure 2. Output characteristics

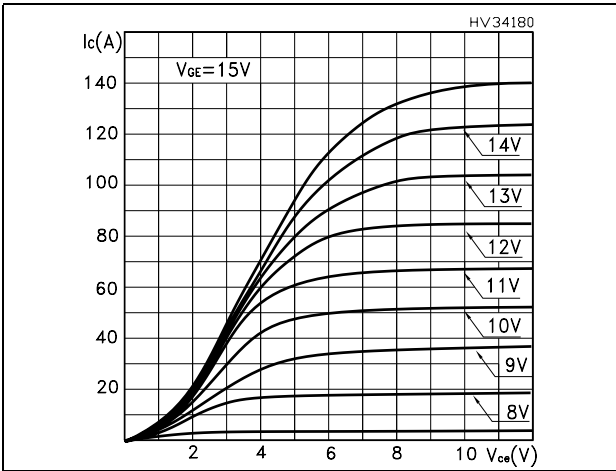


Figure 3. Transfer characteristics

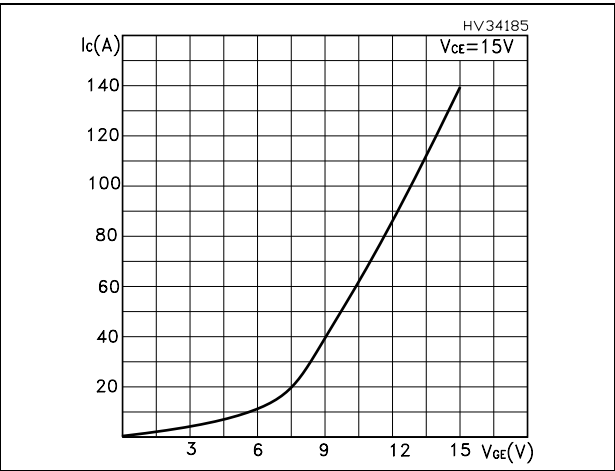


Figure 4. Transconductance

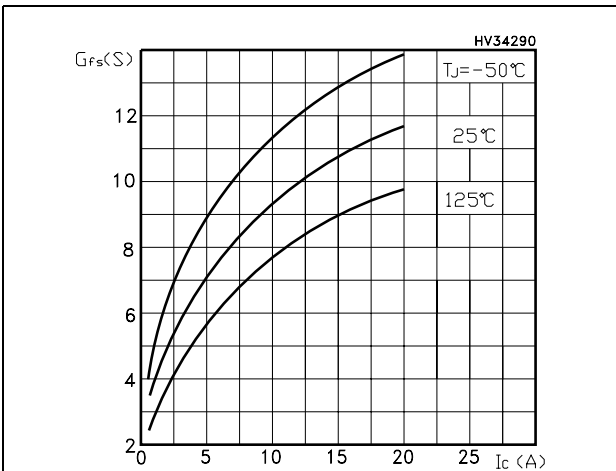


Figure 5. Collector-emitter on voltage vs temperature

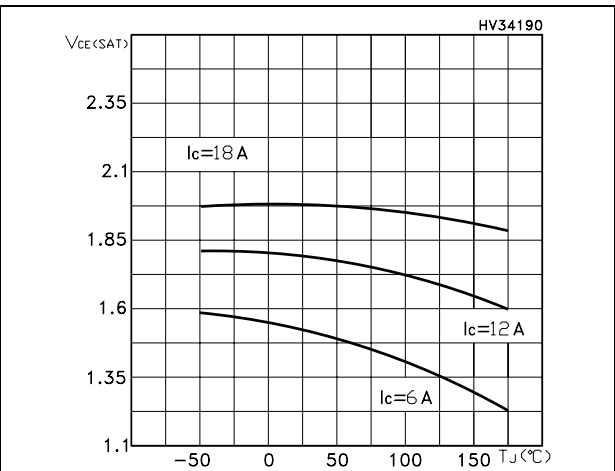


Figure 6. Gate charge vs gate-source voltage

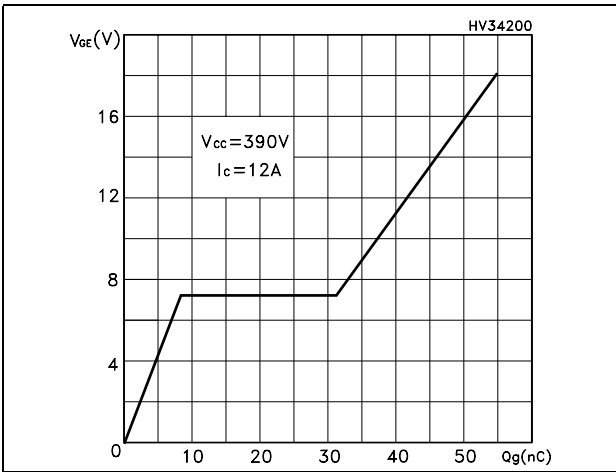


Figure 7. Capacitance variations

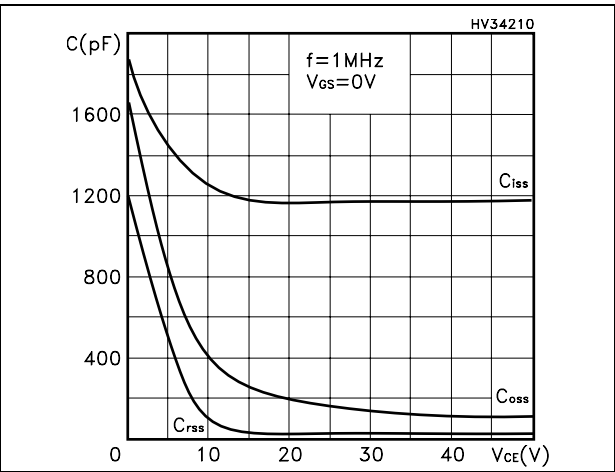


Figure 8. Normalized gate threshold voltage vs temperature

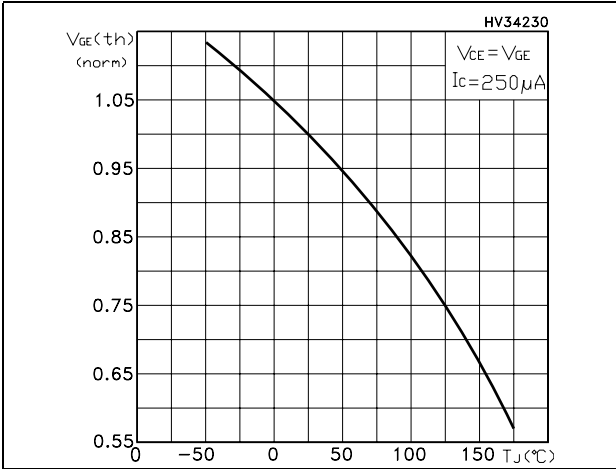


Figure 9. Collector-emitter on voltage vs collector current

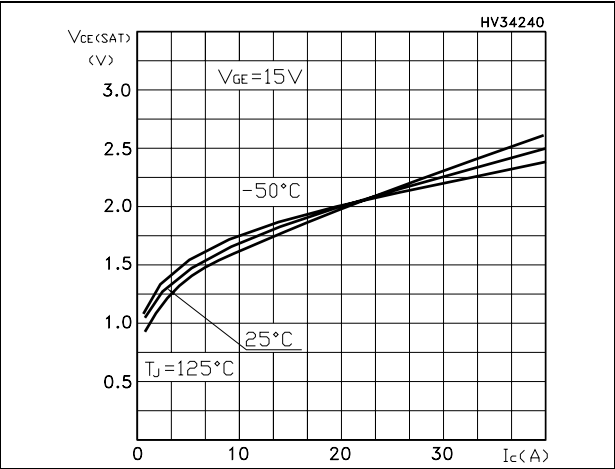


Figure 10. Normalized breakdown voltage vs temperature

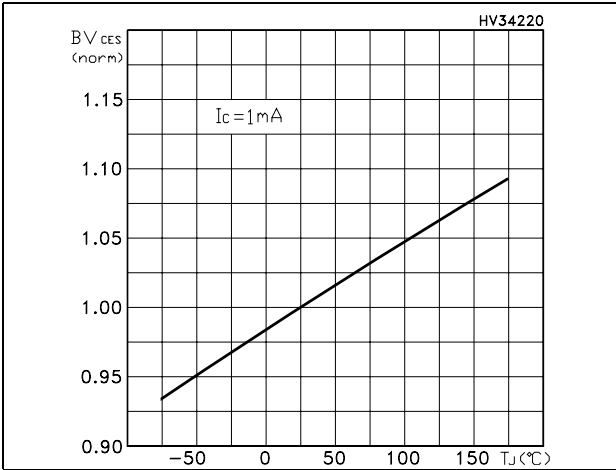


Figure 11. Switching losses vs temperature

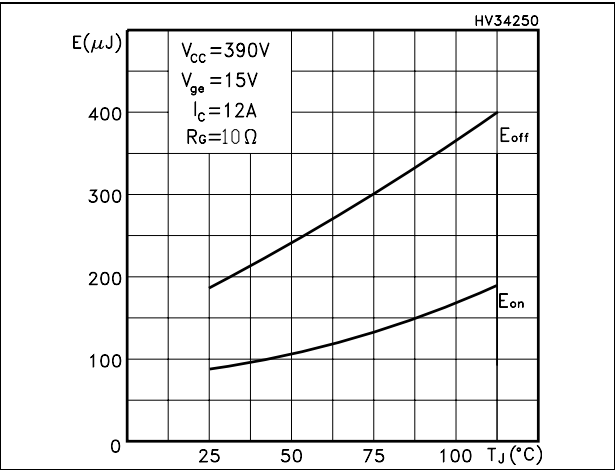


Figure 12. Switching losses vs gate resistance

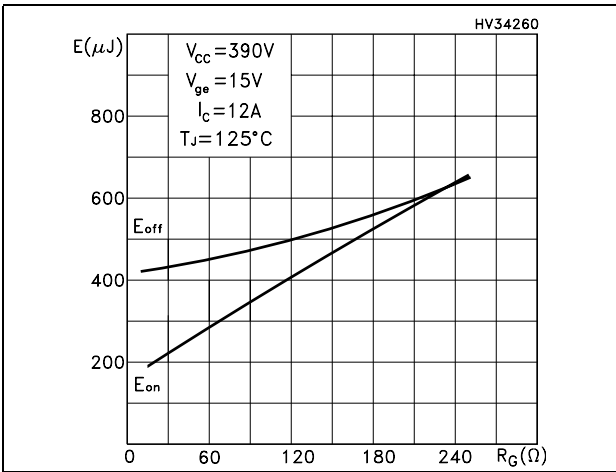


Figure 13. Switching losses vs collector current

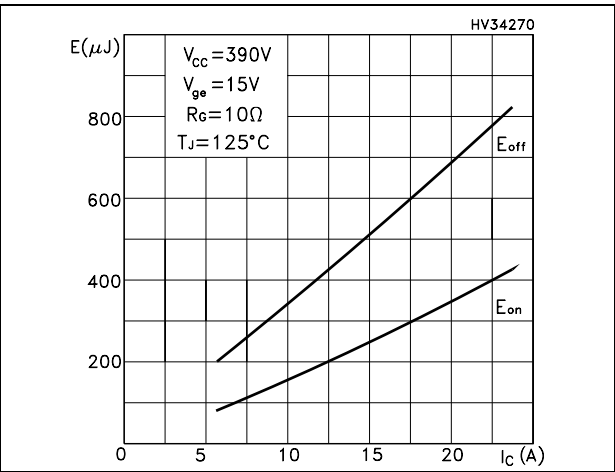


Figure 14. Turn-off SOA

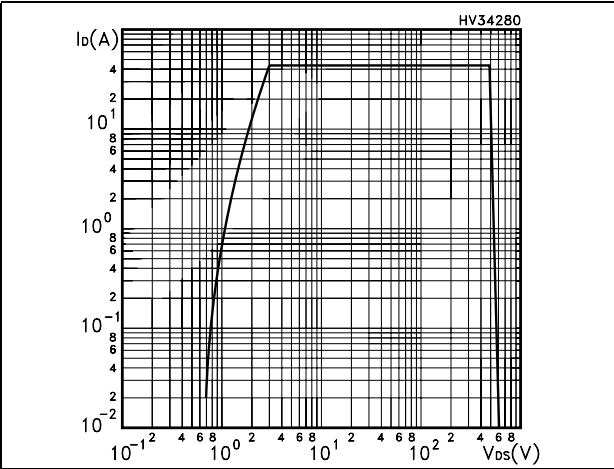


Figure 15. Thermal impedance for TO-220

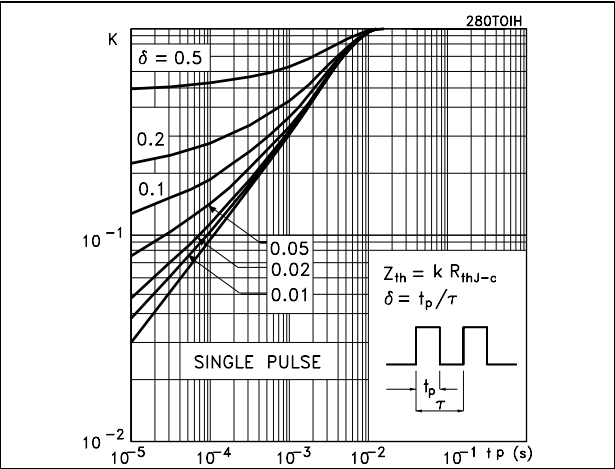
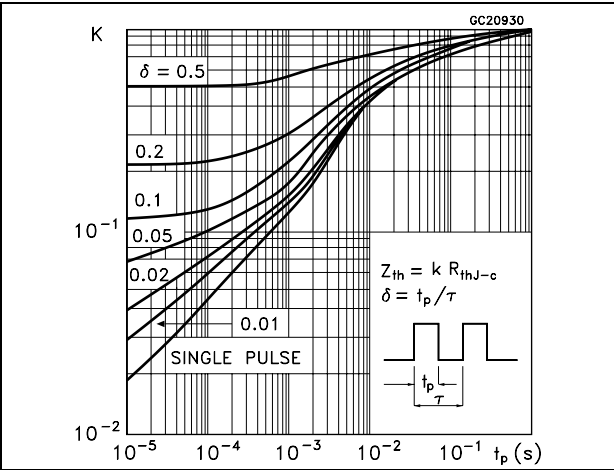


Figure 16. Thermal impedance for TO-247





### 3 Test circuit

Figure 17. Test circuit for inductive load switching

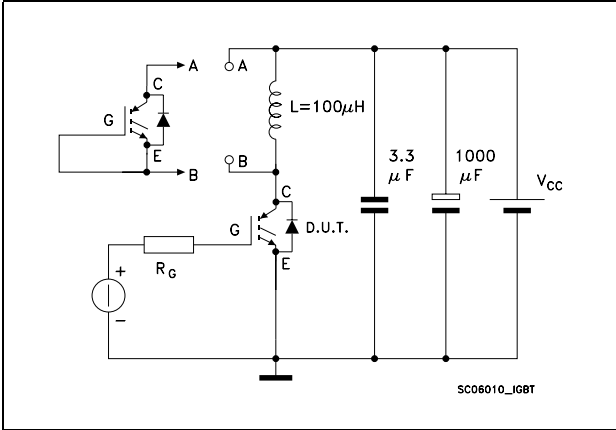


Figure 18. Gate charge test circuit

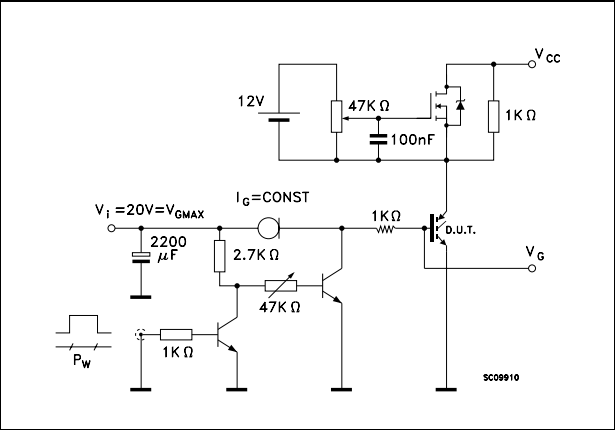
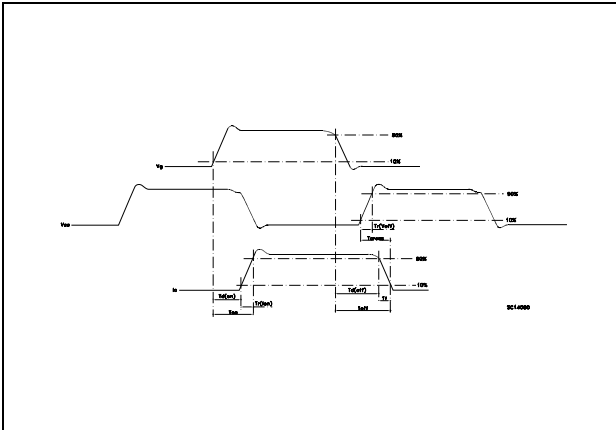


Figure 19. Switching waveform

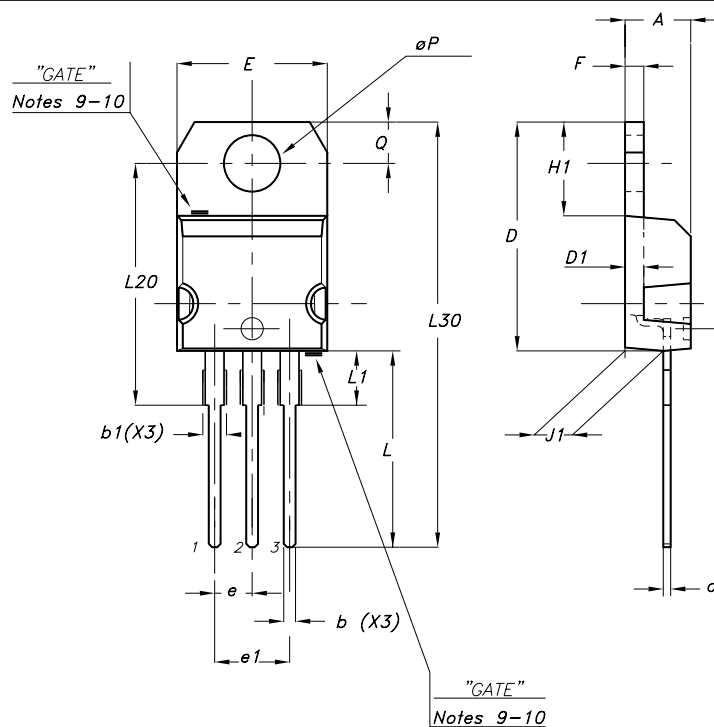


## 4      **Package mechanical data**

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: [www.st.com](http://www.st.com)

## TO-220 mechanical data

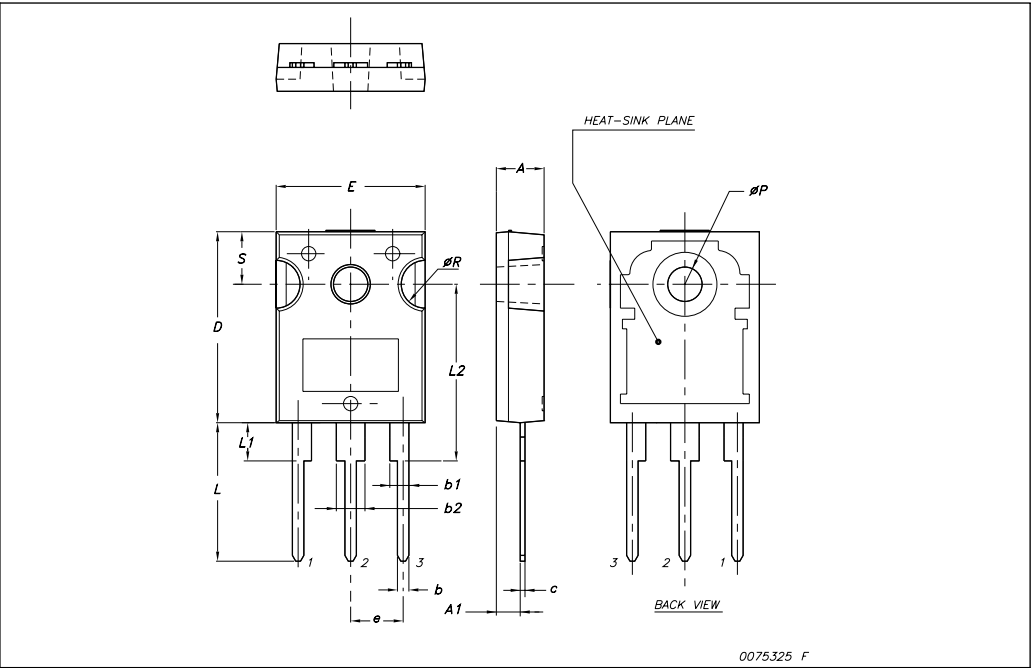
| Dim | mm    |       |       | inch  |       |       |
|-----|-------|-------|-------|-------|-------|-------|
|     | Min   | Typ   | Max   | Min   | Typ   | Max   |
| A   | 4.40  |       | 4.60  | 0.173 |       | 0.181 |
| b   | 0.61  |       | 0.88  | 0.024 |       | 0.034 |
| b1  | 1.14  |       | 1.70  | 0.044 |       | 0.066 |
| c   | 0.48  |       | 0.70  | 0.019 |       | 0.027 |
| D   | 15.25 |       | 15.75 | 0.6   |       | 0.62  |
| D1  |       | 1.27  |       |       | 0.050 |       |
| E   | 10    |       | 10.40 | 0.393 |       | 0.409 |
| e   | 2.40  |       | 2.70  | 0.094 |       | 0.106 |
| e1  | 4.95  |       | 5.15  | 0.194 |       | 0.202 |
| F   | 1.23  |       | 1.32  | 0.048 |       | 0.051 |
| H1  | 6.20  |       | 6.60  | 0.244 |       | 0.256 |
| J1  | 2.40  |       | 2.72  | 0.094 |       | 0.107 |
| L   | 13    |       | 14    | 0.511 |       | 0.551 |
| L1  | 3.50  |       | 3.93  | 0.137 |       | 0.154 |
| L20 |       | 16.40 |       |       | 0.645 |       |
| L30 |       | 28.90 |       |       | 1.137 |       |
| ØP  | 3.75  |       | 3.85  | 0.147 |       | 0.151 |
| Q   | 2.65  |       | 2.95  | 0.104 |       | 0.116 |



0015988\_Rev\_R

TO-247 Mechanical data

| Dim. | mm.   |       |       |
|------|-------|-------|-------|
|      | Min.  | Typ   | Max.  |
| A    | 4.85  |       | 5.15  |
| A1   | 2.20  |       | 2.60  |
| b    | 1.0   |       | 1.40  |
| b1   | 2.0   |       | 2.40  |
| b2   | 3.0   |       | 3.40  |
| c    | 0.40  |       | 0.80  |
| D    | 19.85 |       | 20.15 |
| E    | 15.45 |       | 15.75 |
| e    |       | 5.45  |       |
| L    | 14.20 |       | 14.80 |
| L1   | 3.70  |       | 4.30  |
| L2   |       | 18.50 |       |
| øP   | 3.55  |       | 3.65  |
| øR   | 4.50  |       | 5.50  |
| S    |       | 5.50  |       |



## 5 Revision history

**Table 8. Document revision history**

| Date        | Revision | Changes                                                                       |
|-------------|----------|-------------------------------------------------------------------------------|
| 31-Jan-2008 | 1        | Initial release.                                                              |
| 28-May-2008 | 2        | Inserted new drawing: <a href="#">Figure 16: Thermal impedance for TO-247</a> |

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